

PNP DUAL SILICON TRANSISTOR

Qualified per MIL-PRF-19500/496

Devices

2N5795

2N5796
2N5796U

Qualified Level

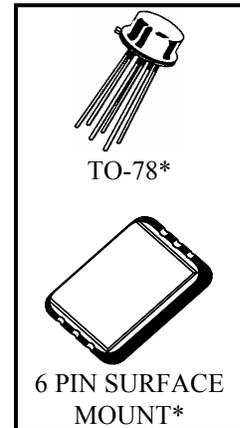
JAN
JANTX
JANTXV

MAXIMUM RATINGS

Ratings	Symbol	Value		Units
Collector-Emitter Voltage	V_{CEO}	60		Vdc
Collector-Base Voltage	V_{CBO}	60		Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current	I_C	600		mAdc
		One⁽¹⁾ Section	Both⁽²⁾ Sections	
Total Power Dissipation @ $T_A = +25^{\circ}\text{C}$	P_T	0.5	0.6	W
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +175		$^{\circ}\text{C}$

1) Derate linearly 2.86 mW/ $^{\circ}\text{C}$ for $T_A \geq +25^{\circ}\text{C}$

2) Derate linearly 3.43 mW/ $^{\circ}\text{C}$ for $T_A \geq +25^{\circ}\text{C}$



*See MILPRF19500/496 for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 10 \text{ mAdc}$	$V_{(BR)CEO}$	60		Vdc
Collector-Base Cutoff Current $V_{CB} = 50 \text{ Vdc}$ $V_{CBO} = 60 \text{ Vdc}$	I_{CBO}		10 10	ηAdc μAdc
Emitter-Base Cutoff Current $V_{EB} = 3.0 \text{ Vdc}$ $V_{EB} = 5.0 \text{ Vdc}$	I_{EBO}		100 10	ηAdc μAdc

2N5795, 2N5796 JAN SERIES

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
ON CHARACTERISTICS (1)				
Forward-Current Transfer Ratio $I_C = 100 \mu\text{A dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 1.0 \text{ mA dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 10 \text{ mA dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 150 \text{ mA dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 300 \text{ mA dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 150 \text{ mA dc}, V_{CE} = 1.0 \text{ V dc}$	2N5795	40 40 40 40 20 20	150	
$I_C = 100 \mu\text{A dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 1.0 \text{ mA dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 10 \text{ mA dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 150 \text{ mA dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 300 \text{ mA dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 150 \text{ mA dc}, V_{CE} = 1.0 \text{ V dc}$	2N5796 2N5796U	75 100 100 100 50 50	300	
Collector-Emitter Saturation Voltage $I_C = 150 \text{ mA dc}, I_B = 15 \text{ mA dc}$ $I_C = 500 \text{ mA dc}, I_B = 50 \text{ mA dc}$	$V_{CE(sat)}$		0.4 1.6	Vdc
Base-Emitter Saturation Voltage $I_C = 150 \text{ mA dc}, I_B = 15 \text{ mA dc}$ $I_C = 500 \text{ mA dc}, I_B = 50 \text{ mA dc}$	$V_{BE(sat)}$		1.3 2.6	Vdc

DYNAMIC CHARACTERISTICS

Magnitude of Small-Signal Forward Current Transfer Ratio $I_C = 20 \text{ mA dc}, V_{CE} = 20 \text{ V dc}, f = 100 \text{ MHz}$	$ h_{fe} $	2.0	10	
Output Capacitance $V_{CB} = 10 \text{ V dc}, I_E = 0, 100 \text{ kHz} \leq f \leq 1.0 \text{ MHz}$	C_{obo}		8.0	pF
Input Capacitance $V_{EB} = 2.0 \text{ V dc}, I_C = 0, 100 \text{ kHz} \leq f \leq 1.0 \text{ MHz}$	C_{ibo}		25	pF

SWITCHING CHARACTERISTICS

Turn-On Time $V_{CC} = 30 \text{ V dc}; I_C = 150 \text{ mA dc}; I_{B1} = 15 \text{ mA dc}$	t_{on}		50	ns
Turn-Off Time $V_{CC} = 30 \text{ V dc}; I_C = 150 \text{ mA dc}; I_{B1} = I_{B2} = 15 \text{ mA dc}$	t_{off}		140	ns

1) Pulse Test: Pulse Width = 300μs, Duty Cycle ≤ 2.0%.

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